

900V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information			
Device	Package	Marking	
CS4N90F	TO-220F	CS4N90F	
CS4N90P	TO-220	CS4N90P	

TO-220F GDS	TO-220 GDS

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter	Cumhal	Va			
Farameter	Symbol	TO-220F	TO-220	Unit	
Drain-Source Voltage ($V_{GS} = 0V$)	V _{DSS}	900		V	
Continuous Drain Current	I _D	4		A	
Pulsed Drain Current (note1)	I _{DM}	16		A	
Gate-Source Voltage	V _{GSS}	±	30	V	
Single Pulse Avalanche Energy (note2)	E _{AS}	125		mJ	
Avalanche Current (note1)	I _{AS}	5		А	
Repetitive Avalanche Energy (note1)	E _{AR}	75		mJ	
Power Dissipation ($T_c = 25^{\circ}C$)	P _D	25	70	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~	-+150	٥C	

Thermal Resistance				
Desemptor	Symbol	Va	1114	
Parameter		TO-220F	TO-220	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	5	1.78	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	K/W



CS4N90F, CS4N90P

Specifications $T_J = 25^{\circ}C$, unless otherwise noted							
Parameter Symbol	Symbol	Test Conditions	Value			Unit	
		Min.	Тур.	Max.	Unit		
Static				-	-		
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	900			V	
Zero Gate Voltage Drain Current		$V_{DS} = 900V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1		
Zero Gale Voltage Drain Gurrent	I _{DSS}	$V_{DS} = 720V, V_{GS} = 0V, T_{J} = 125^{\circ}C$			100	μA	
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V	
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V _{GS} = 10V, I _D =2A	-	3	3.5	Ω	
Dynamic							
Input Capacitance	C _{iss}	V = 0V		674		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$ f = 1.0MHz		71			
Reverse Transfer Capacitance	C _{rss}			13			
Total Gate Charge	Q _g			27			
Gate-Source Charge	Q_gs	$V_{DD} = 720V, I_D = 4A, V_{GS} = 10V$		3.5		nC	
Gate-Drain Charge	Q_{gd}			14			
Turn-on Delay Time	t _{d(on)}			37			
Turn-on Rise Time	t _r	V _{DD} = 450V, I _D = 4A,		15			
Turn-off Delay Time	t _{d(off)}	$R_G = 25 \Omega$		144		ns	
Turn-off Fall Time	t _f			36			
Drain-Source Body Diode Character	istics						
Continuous Body Diode Current	۱ _s	T _C = 25 °C			4	^	
Pulsed Diode Forward Current	I _{SM}				16	A	
Body Diode Voltage	V_{SD}	$T_{J} = 25^{\circ}C, I_{SD} = 2A, V_{GS} = 0V$			1.4	V	
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 4A,		1018		ns	
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		2.2		μC	

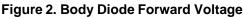
Notes

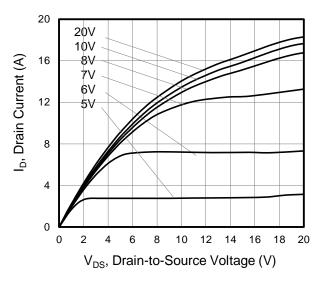
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25°C)







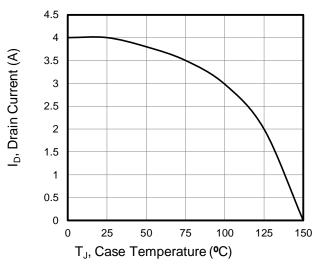
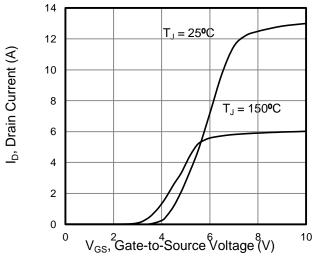


Figure 5. Transfer Characteristics



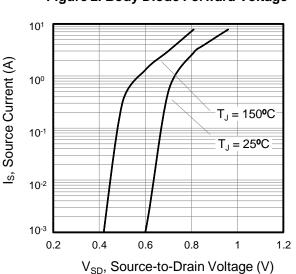


Figure 4. BV_{DSS} Variation vs. Temperature

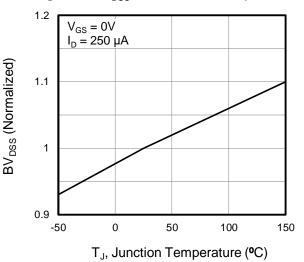
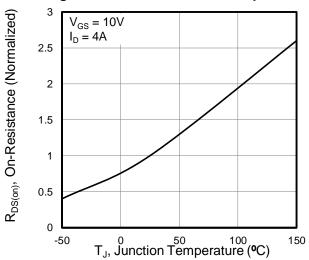
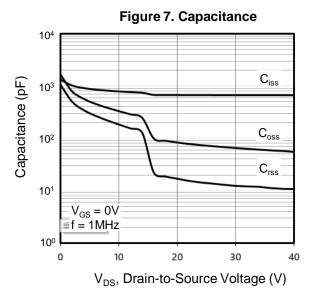


Figure 6. On-Resistance vs. Temperature

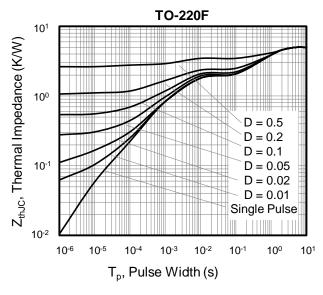




Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted







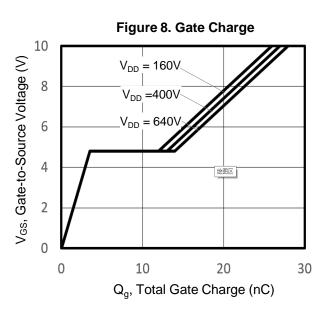
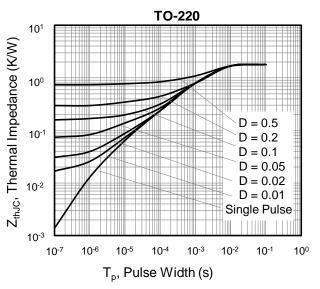


Figure 10. Transient Thermal Impedance







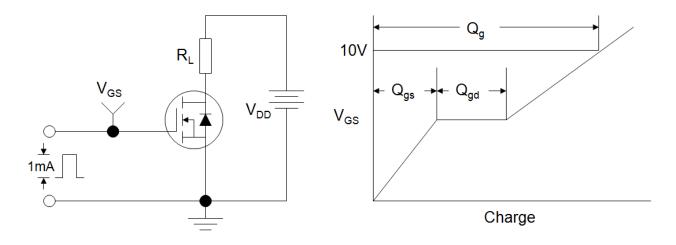


Figure B: Resistive Switching Test Circuit and Waveform

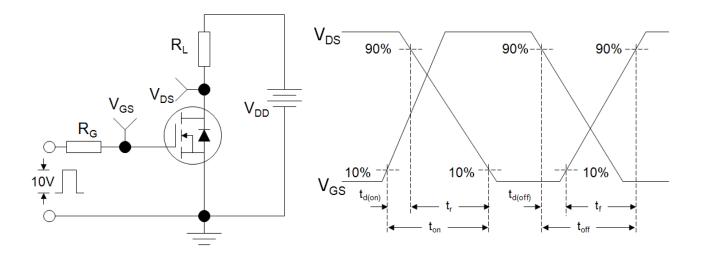
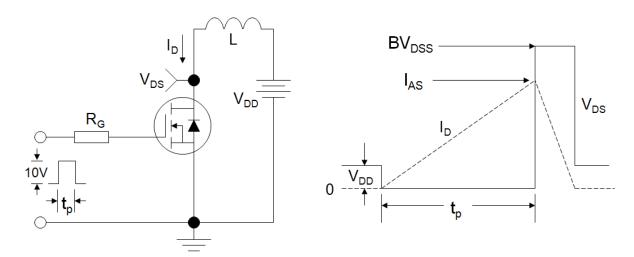


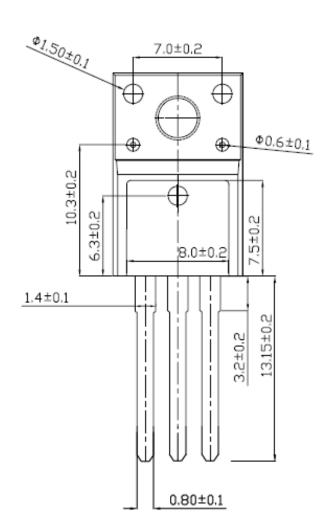
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

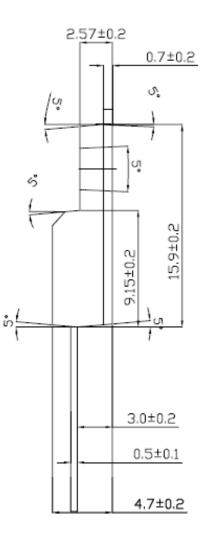






TO-220F

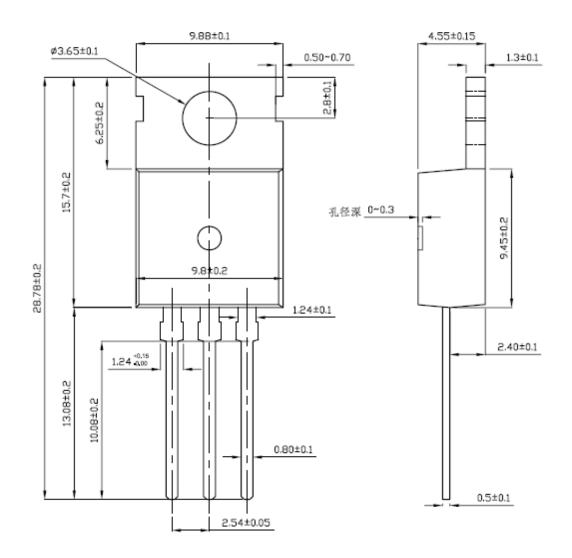








TO-220





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